

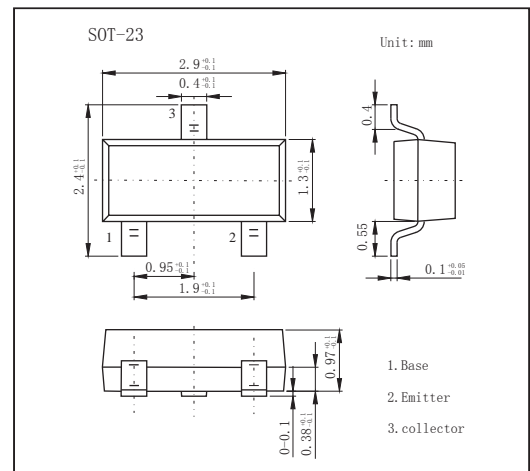
## SOT-23 Plastic-Encapsulate Transistors

### FEATURES

- High Voltage
- NPN Transistors

### MECHANICAL DATA

- Case style:SOT-23 molded plastic
- Mounting position:any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	180	V
Collector-emitter voltage	V <sub>CEO</sub>	160	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Collector current-continuous	I <sub>C</sub>	0.6	A
Collector Power Dissipation	P <sub>C</sub>	300	mW
Junction and storage temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = 100uA, I <sub>E</sub> = 0	180			V
Collector-emitter breakdown voltage *	V <sub>CEO</sub>	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0	160			V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = 10uA, I <sub>C</sub> = 0	6			V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 120 V, I <sub>E</sub> = 0			50	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 4.0V, I <sub>C</sub> = 0			50	nA
DC current gain *	h <sub>FE</sub>	I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5 V	80			
		I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5 V	100		300	
		I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 5 V	50			
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA			0.5	V
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 5.0 mA			1.0	V
Transistor frequency	f <sub>r</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz	100			MHz

\* Pulse Test: Pulse Width = 300 μs, Duty Cycle=2.0%.

# RATINGS AND CHARACTERISTIC CURVES

